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(12) **United States Design Patent**
Sawada

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(54) **POWER SEMICONDUCTOR MODULE**

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(**) Term: **15 Years**

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(52) **U.S. Cl.**
USPC **D13/182**

(58) **Field of Classification Search**

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361/679.01, 713, 728, 736, 760, 761, 772,
361/775, 783, 820; 174/250, 253;
438/15, 25, 26, 51, 55, 63, 64, 106
CPC . H01L 21/00; H01L 2224/42; H01L 2224/43;
H01L 2021/00; H01L 2021/02; H01L
2021/04; H01L 21/4814; H01L 21/4846;
H01L 21/4871; H01L 21/67144; H01L
23/02; H01L 23/13; H01L 23/14; H01L
23/147; H01L 2924/171; H01L
2924/1711; H01L 2924/1715; H01L
2924/17151; H01L 2924/181; H01L
2924/1811; H01L 2924/1815; H01L
2924/19042; H01L 2924/1905; H01L
2224/08054; H01L 23/58; H05B 41/14;
H02B 6/4201; G02B 6/4256; G02B
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G02B 6/428; G02B 6/4281; H05K 1/14;
H05K 1/141; H05K 1/142; H05K 1/144;
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H05K 1/026

See application file for complete search history.

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(57) **CLAIM**

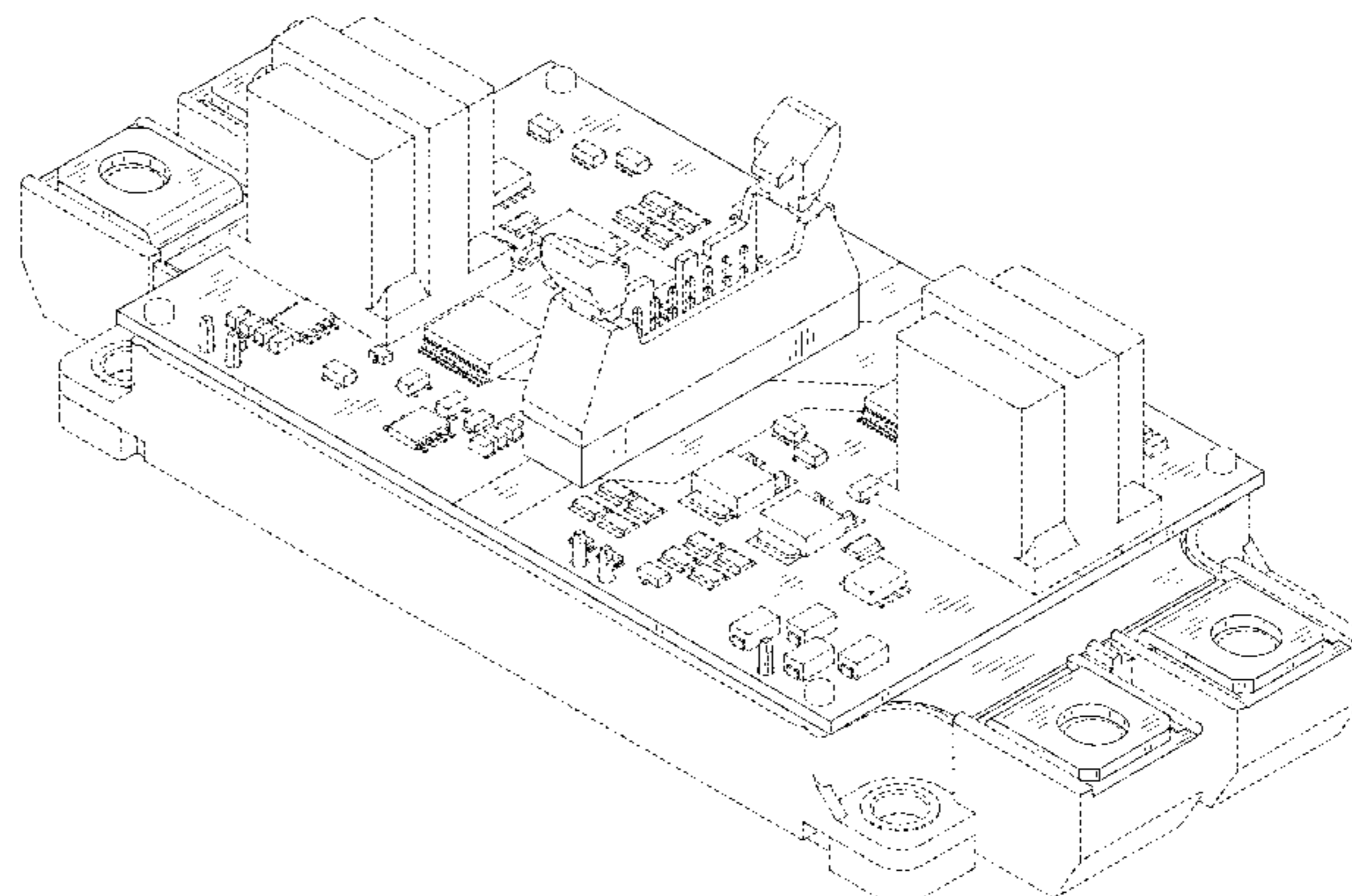
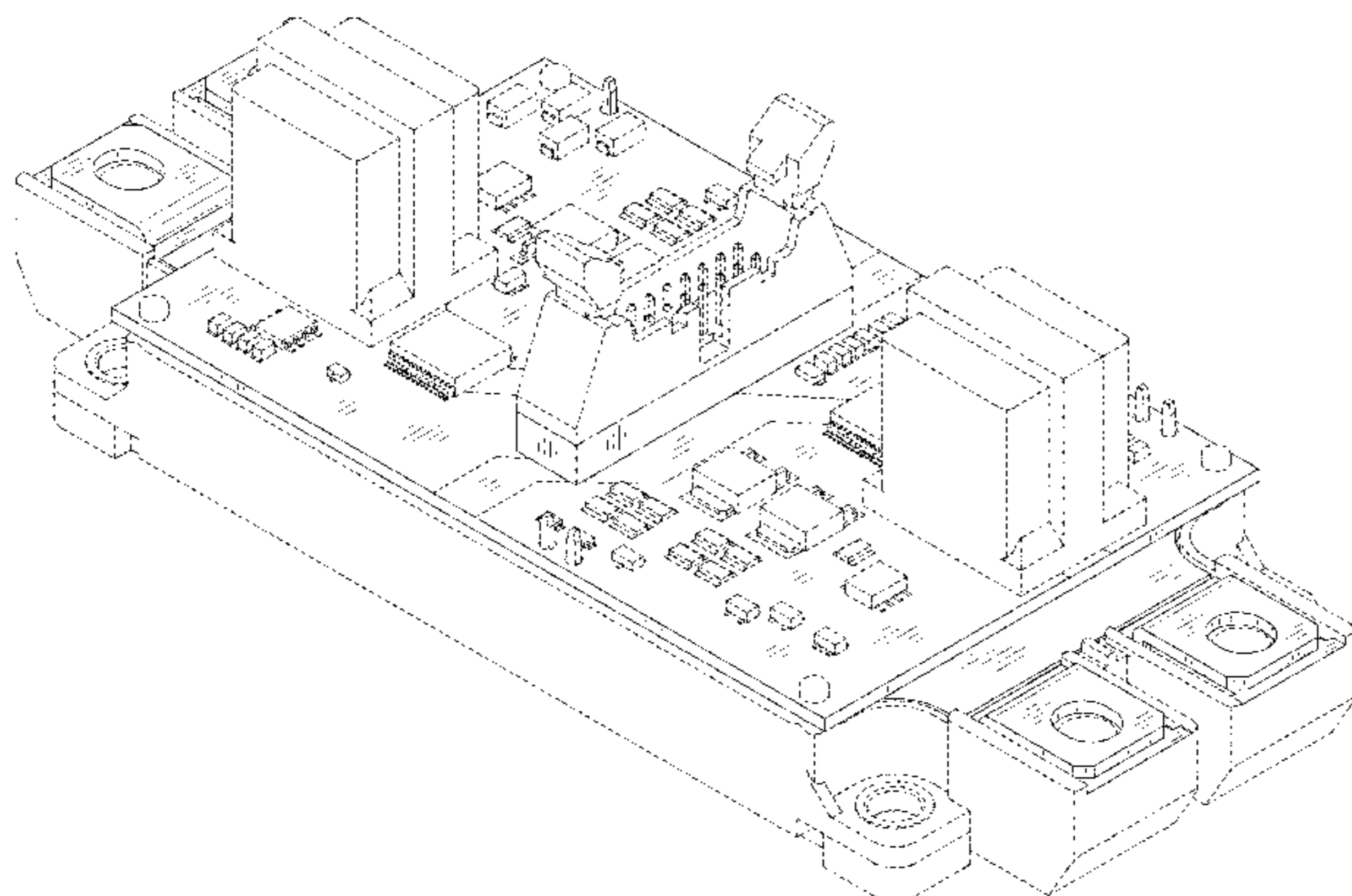
The ornamental design for a power semiconductor module,
as shown and described.

DESCRIPTION

FIG. 1 is a front, top, and right side perspective view of a
power semiconductor module showing my new design;
FIG. 2 is a rear, top, and left side perspective view thereof;
FIG. 3 is a front view thereof;
FIG. 4 is a rear view thereof;
FIG. 5 is a top plan view thereof;
FIG. 6 is a bottom plan view thereof;
FIG. 7 is a right side view thereof; and,
FIG. 8 is a left side view thereof.

The features shown in broken lines in the drawings depict
portions of the article that form no part of the claimed
design. The dash-dotted lines denote the boundary of the
claim and form no part of the claimed design. The broken
lines within the area encompassed by the solid lines form no
part of the claimed design.

1 Claim, 8 Drawing Sheets



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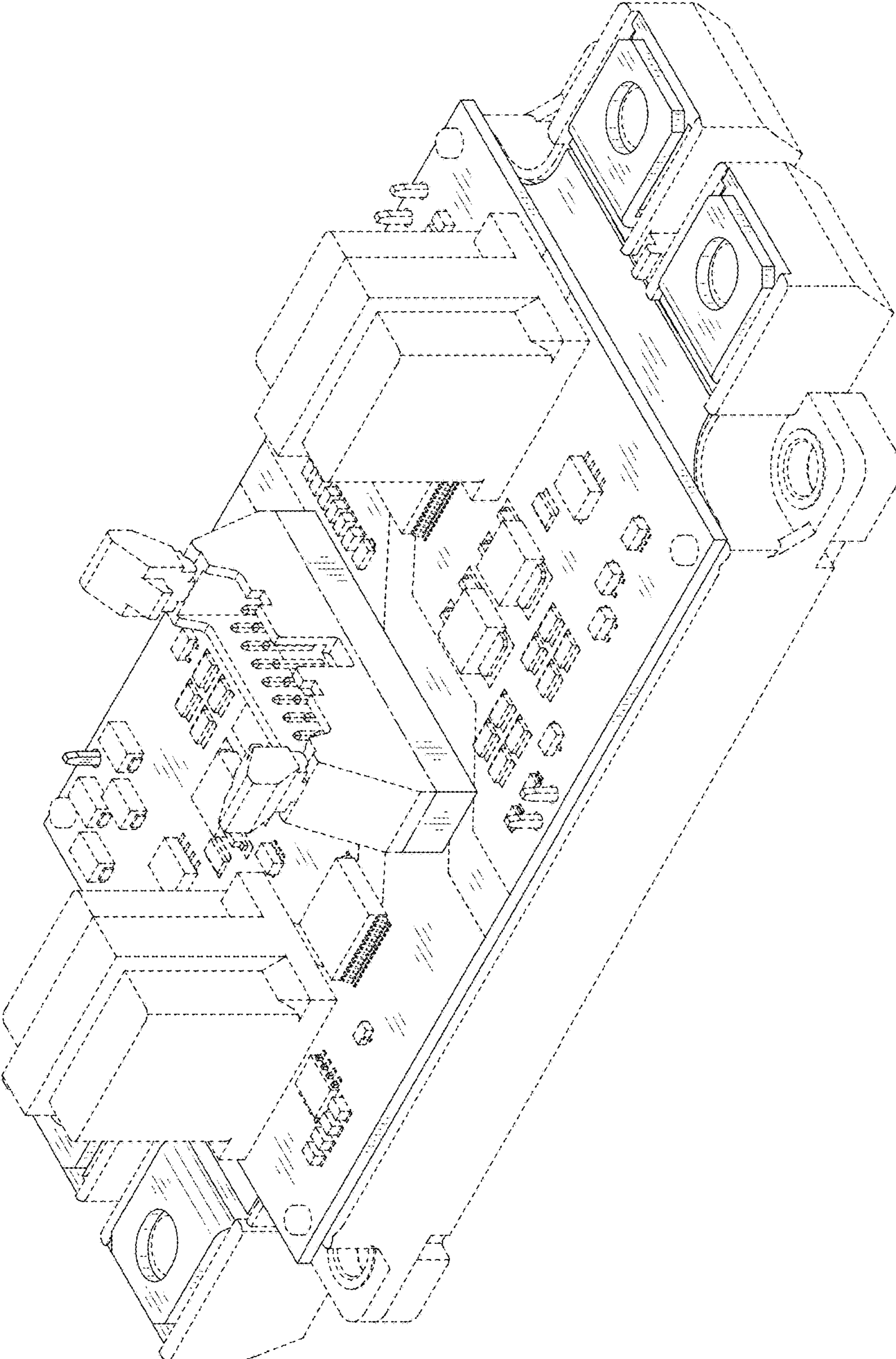


FIG.1

FIG.2

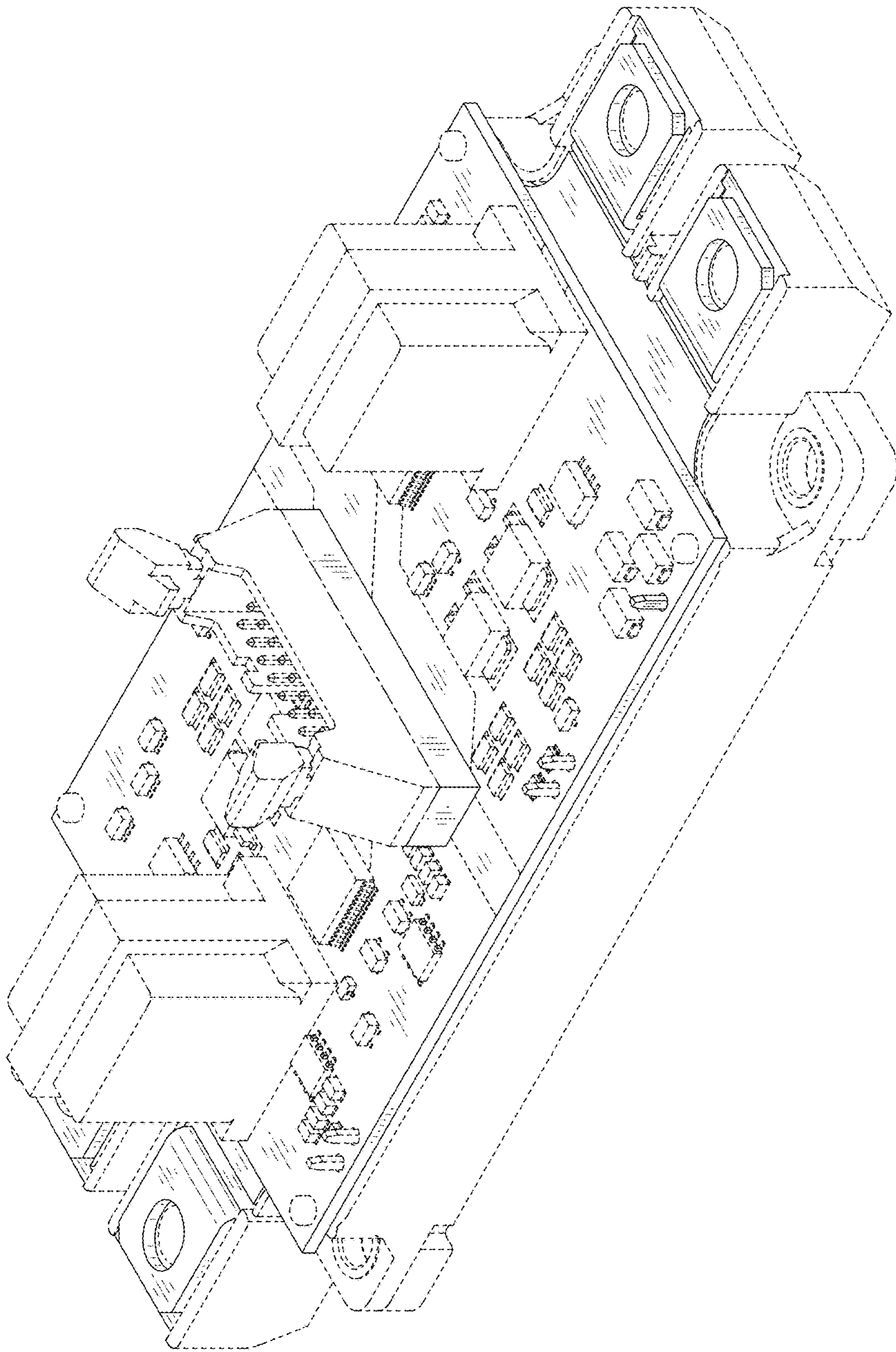


FIG.3

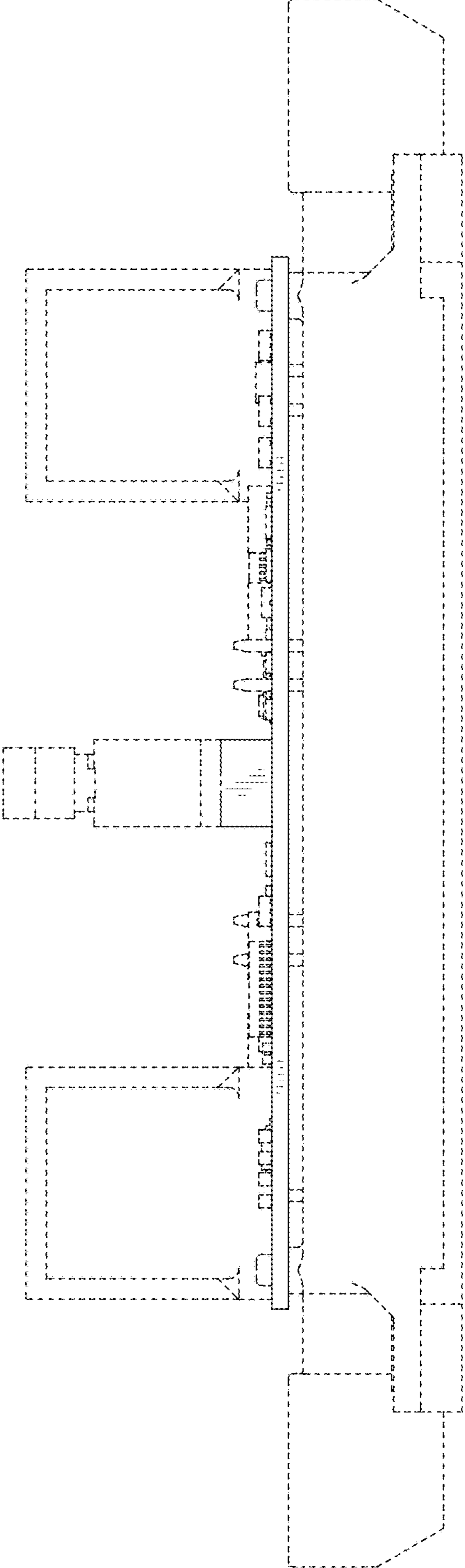
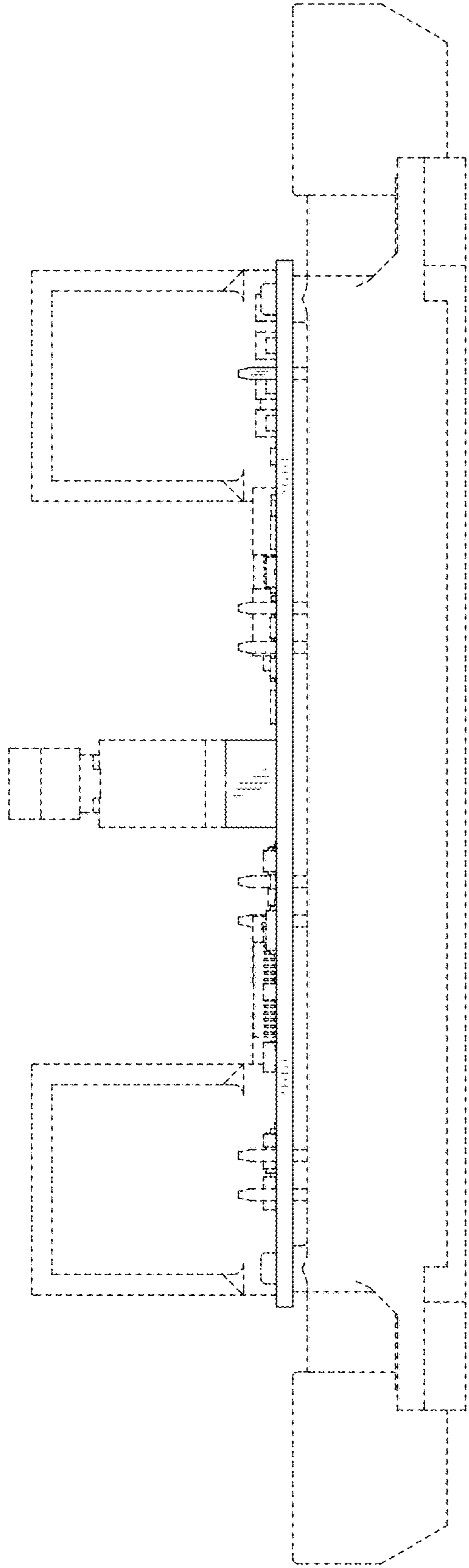


FIG.4



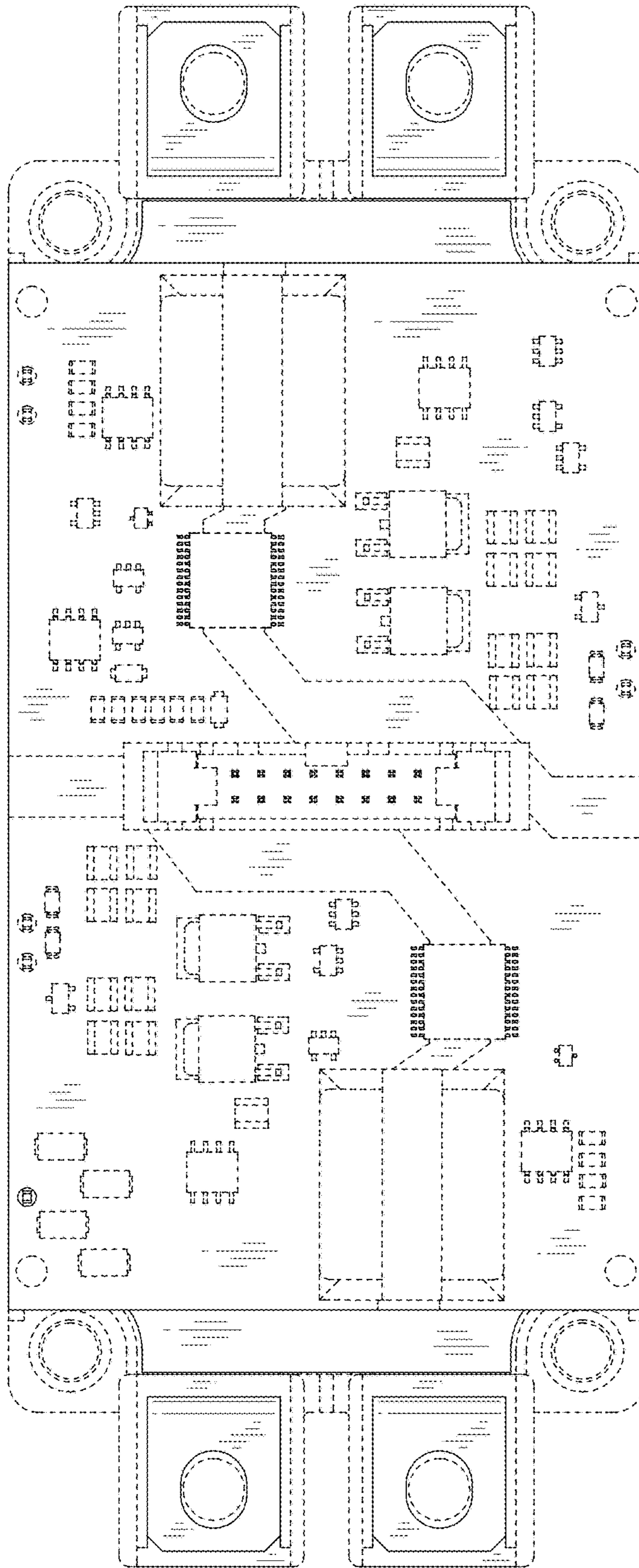


FIG.5

FIG.6

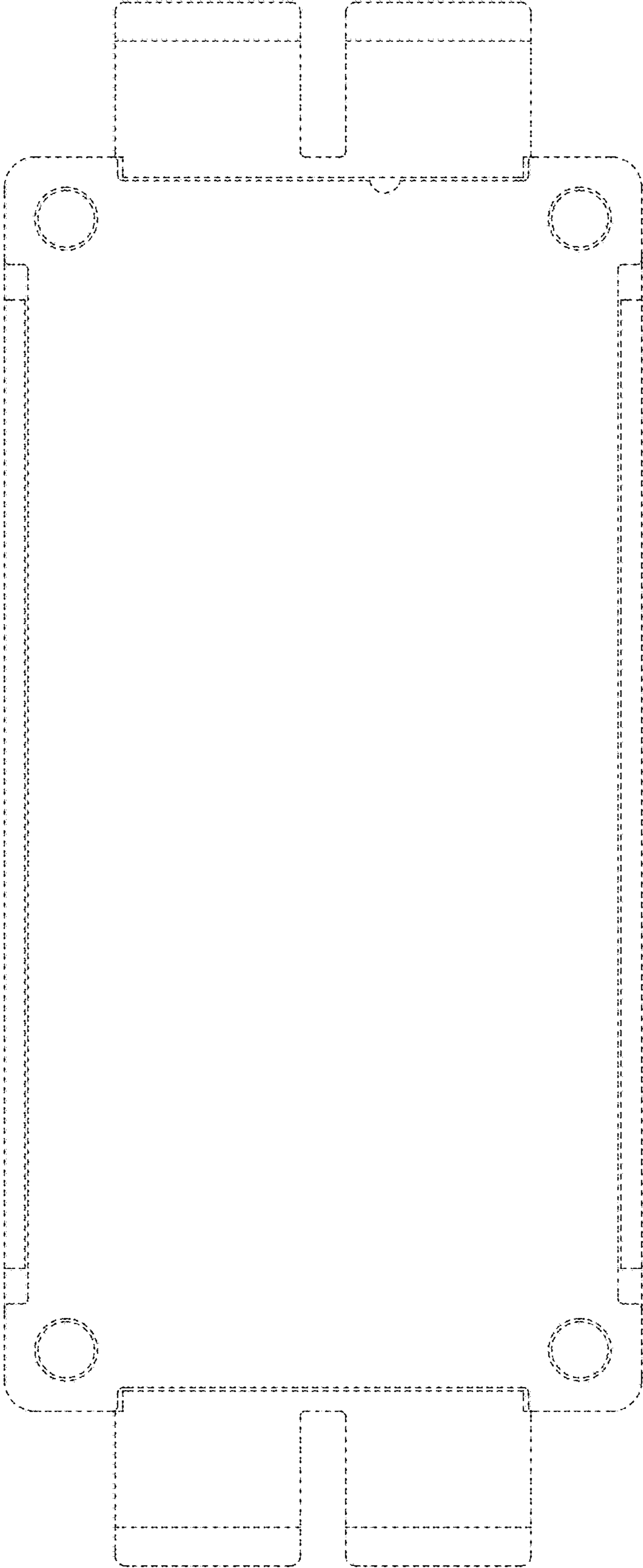


FIG. 7

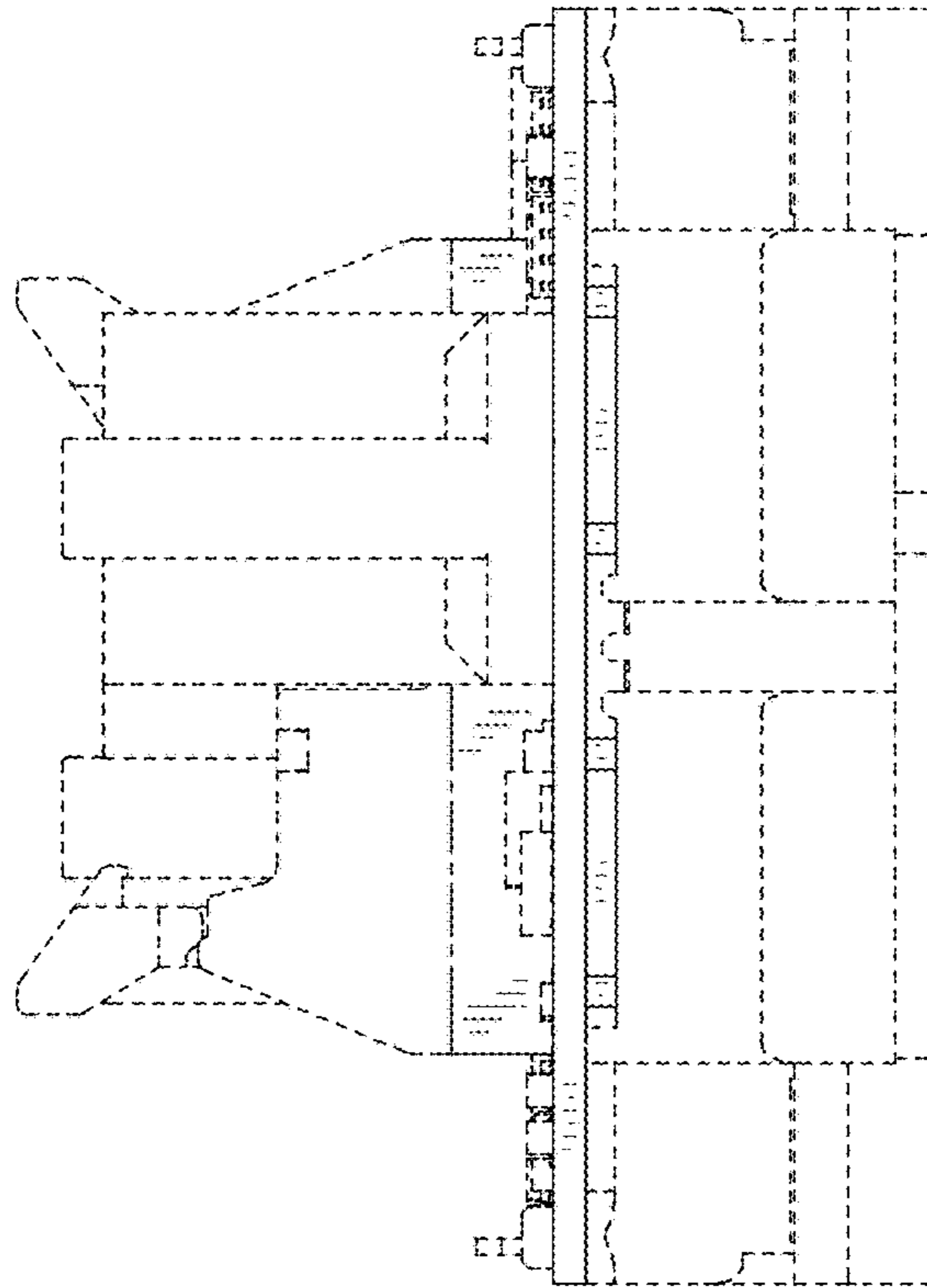


FIG. 8

